

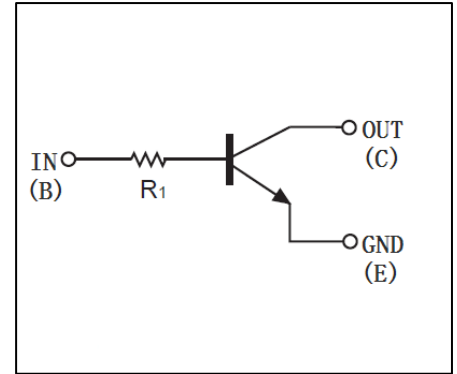
DTC144TE/DTC144TUA DTC144TKA /DTC144TCK

DIGITAL TRANSISTOR (NPN)

FEATURES

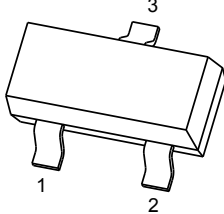
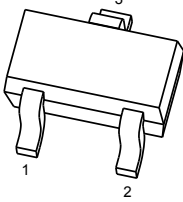
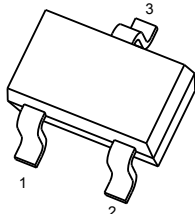
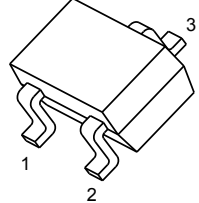
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input.They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy

• Equivalent Circuit



MARKING:06

PIN CONNENCTIONS and MARKING

DTC144TCK 	SOT-23 1. IN 2. GND 3. OUT	DTC144TE 	SOT-523 1. IN 2. GND 3. OUT
DTC144TUA 	SOT-323 1. IN 2. GND 3. OUT	DTC144TKA 	SOT-23-3L 1. IN 2. GND 3. OUT

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Limits(DTC144T□)				Unit
		E	UA	KA	CA	
V _{CBO}	Collector-Base Voltage	50				V
V _{CEO}	Collector-Emitter Voltage	50				V
V _{EBO}	Emitter-Base Voltage	5				V
I _C	Collector Current -Continuous	100				mA
P _D	Power Dissipation	150	200	200	200	mW
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150				°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =50V, I _E =0			0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =5mA, I _B =0.5mA			0.3	V
DC current gain	h _{FE}	V _{CE} =5V, I _C =1mA	100			
Input resistor	R ₁		32.9	47	61.1	kΩ
Transition frequency	f _T	V _{CE} =10V, I _E =-5mA, f=100MHz		250		MHz

Typical Characteristics

